

Status of C6D6+SiPM developments

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The n_TOF Collaboration

- Objectives of a new C6D6 design
 - Neutron sensitivity
 - Electrical signal response
 - B-field insensitivity

QUICK SUMMARY

- **Readout electronics for SiPM and fast signals**
- **Encapsulation optimization**
- **Schedule and possible proposals**

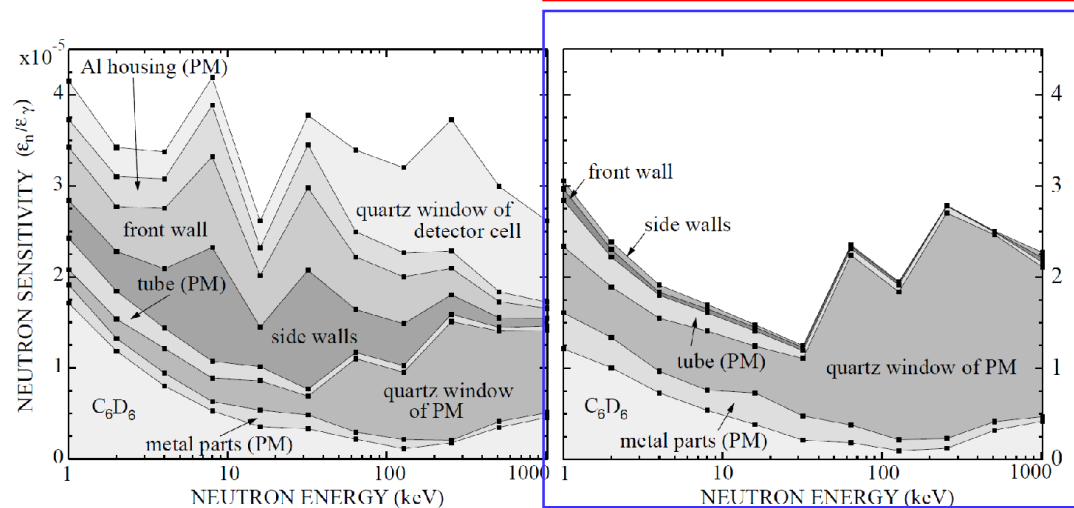
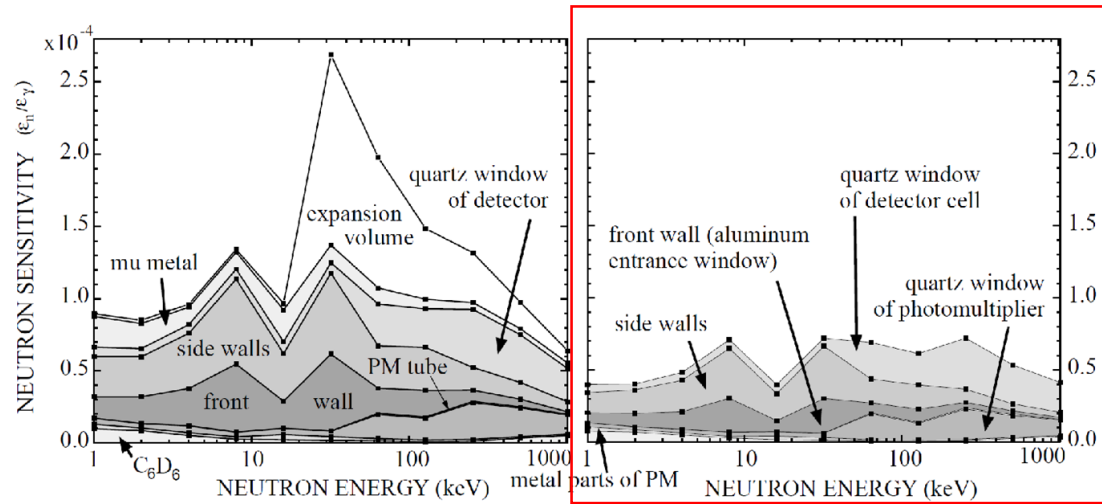
ONGOING WORK

- Further **reduce the intrinsic Neutron Sensitivity** (compared to state-of-the-art C6D6)
- Better **suited for high CRs and γ -flash (EAR2)** by reducing volume (1/4 L6D6) → Better suited for high En-range
- Clean electrical output signals (no VDs → no rebounds → To be tested in the lab during LS2) → **Reliable PSA**
- Fast response, comparable or better than PMTs → Well suited for neutron-TOF
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C6D6/PMT Neutron sensitivity: could it be improved further?

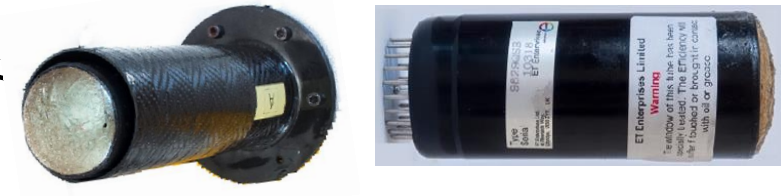
➤ Aspect 1: neutron sensitivity



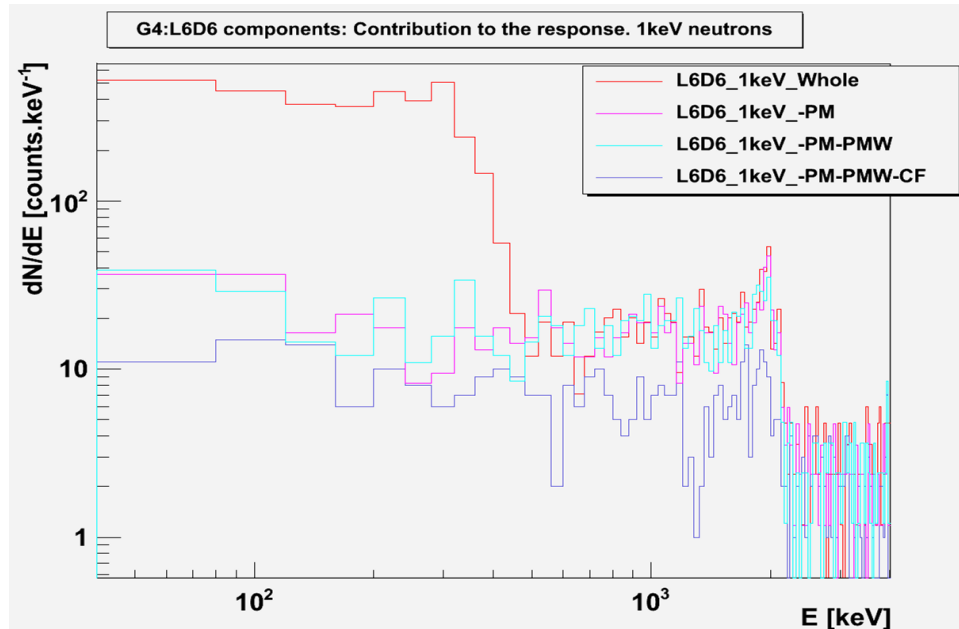
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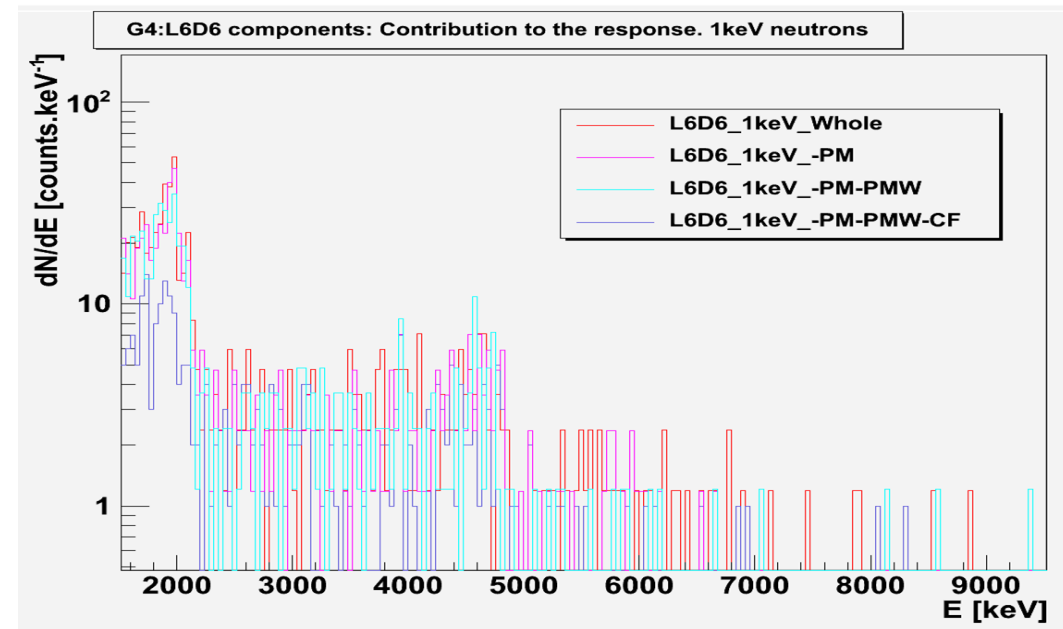
L6D6 Response to Neutrons (C. Guerrero & J.Lerendegui-Marco, U)



➤ Analysis of main contributions to neutron sensitivity of the L6D6 :



PMT is main contributor (E < 500keV)



CF main contribution at ~2.2 MeV

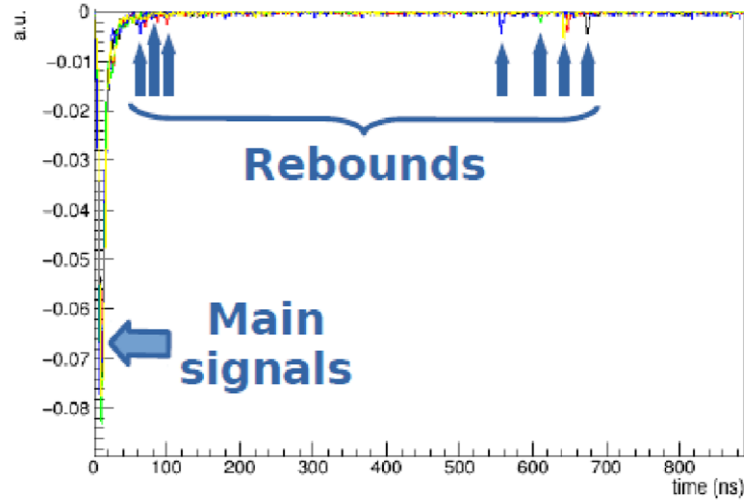
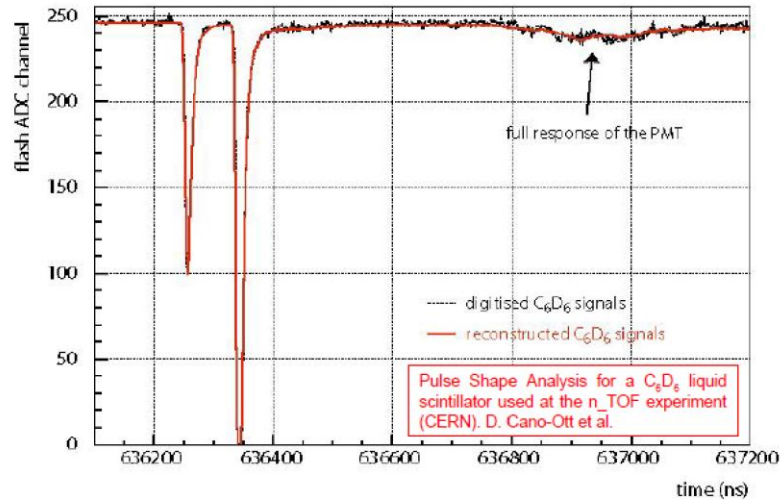
➔ Thus, avoiding PMT (thereby reducing also total amount of CF) should help to reduce NS further down(!)

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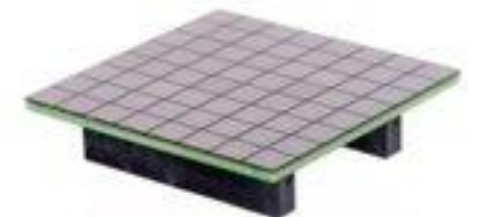
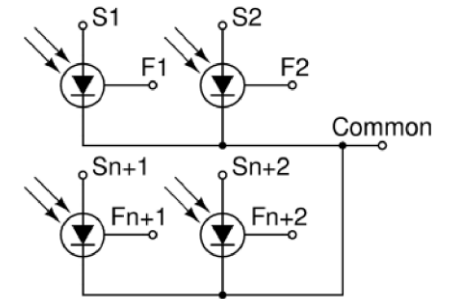
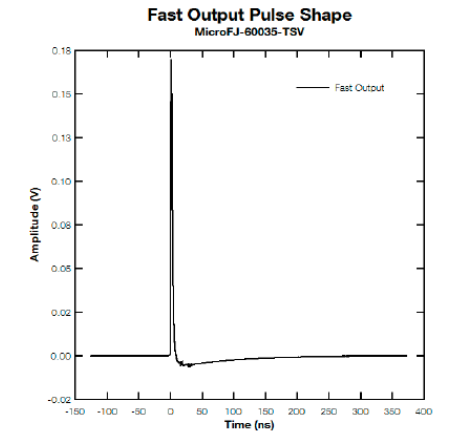
C6D6/PMT response: affected by artifacts (rebounds) probably arising from PMT's Voltage Divider:

→ Aspect 2: ringing and rebounds produce a “dirty” electrical response

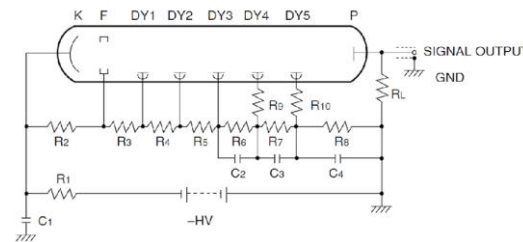
PMT + Voltage Divider:



SiPM:



Hypothesis: Impedance mismatch issues due to voltage divider



Input from **Lucia Gallego**.
After pulse desexcitation:

Meas. Sci. Technol. 7 (1996) 121–135.

J. P. E 10 (1977) Volume 10 1044

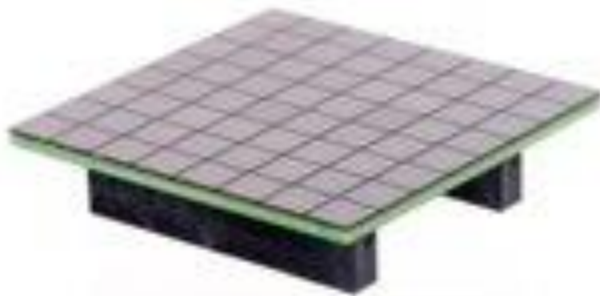
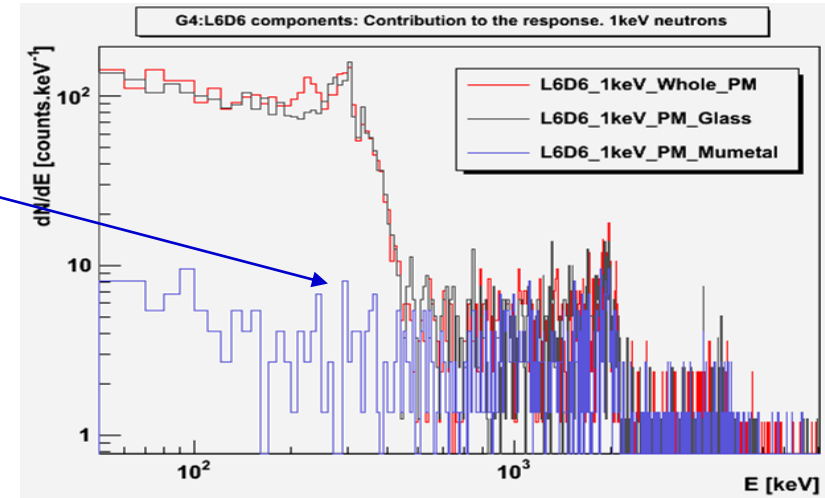
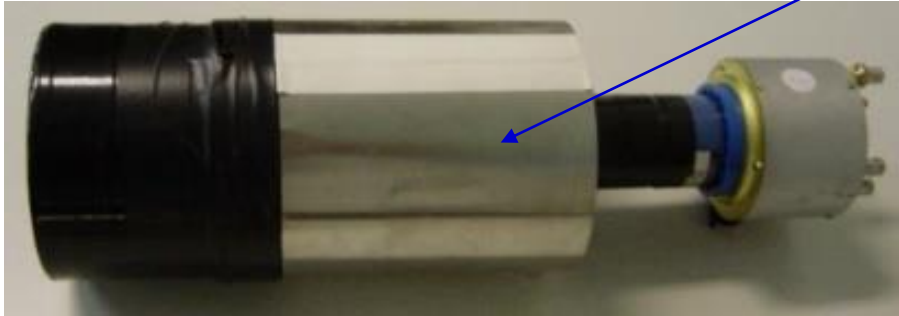
NIM A 574 (2007) 121–126

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C6D6/PMT B-field sensitivity: can we avoid it?

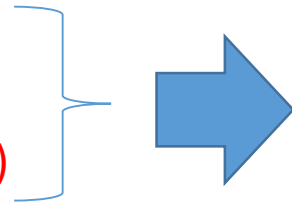
➤ Aspect 3: mu-metal & magnetic fields screening

mu-metal

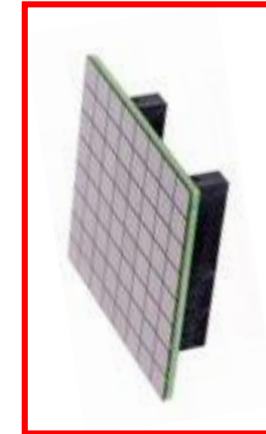
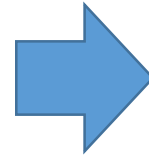


From conventional C6D6/PMT towards C6D6/SiPM: the proposal to develop a new C6D6

- Aspect 1: “dirty” signal response
- Aspect 2: neutron sensitivity (PMT)
- Aspect 3: B-field sensitivity (mu-metal)

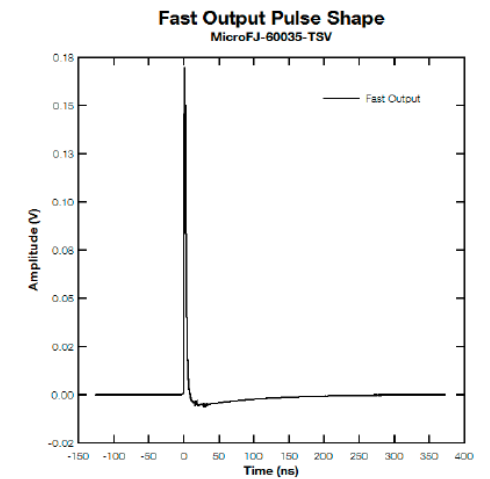


Replace PMT+VD by SiPM



“Mock” prototype of IFIC-C6D6: i6D6

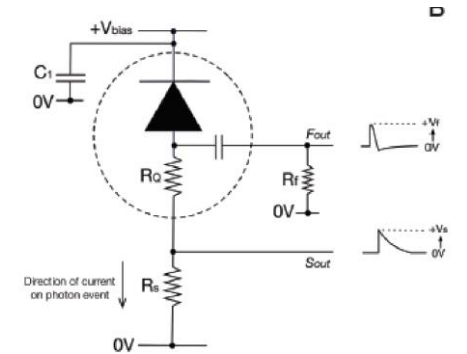
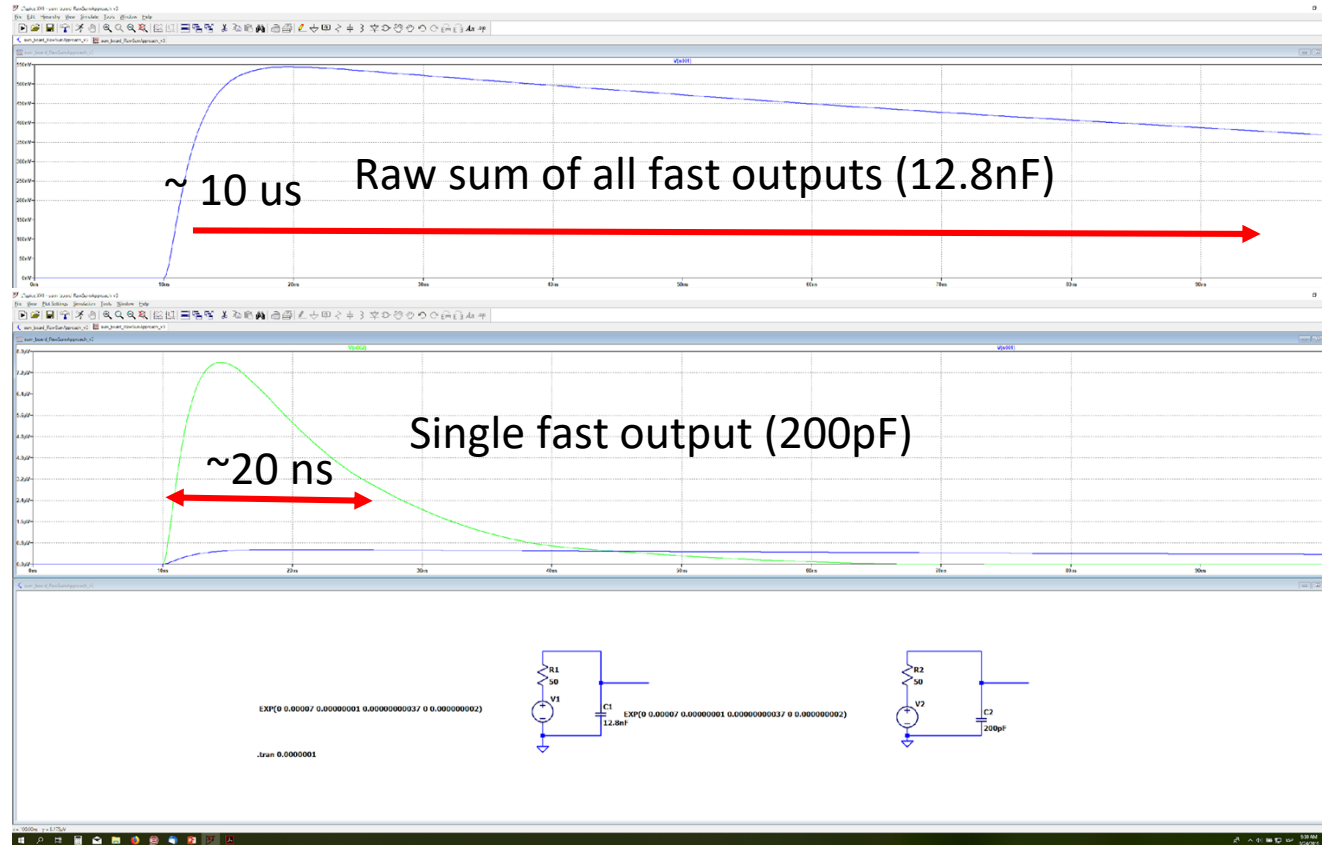
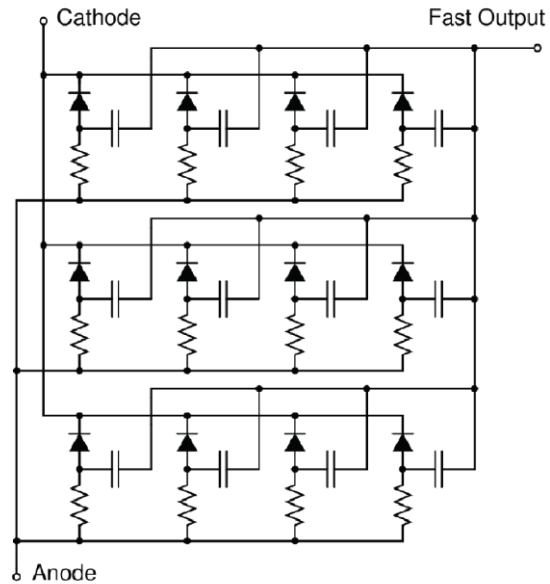
- 250 ml C6D6
- SiPM Sensl 50x50mm²
- 1/4th of L6D6 volumen (four of these make one L6D6)



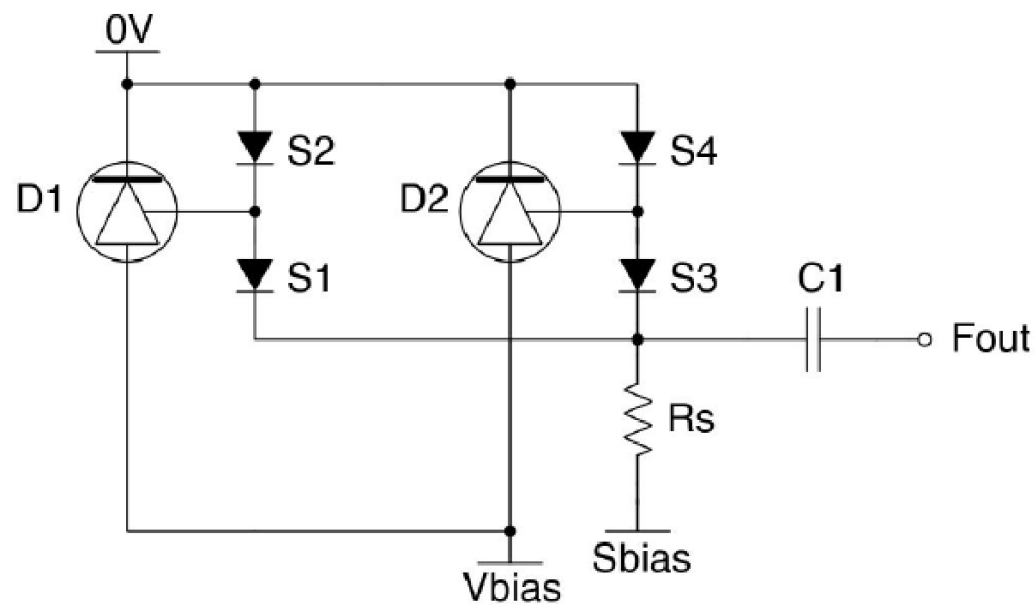
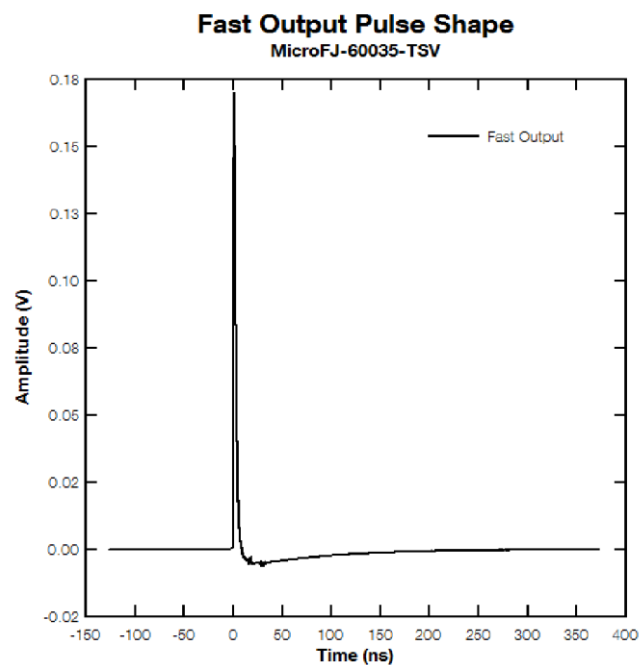
→ Readout electronics design for fast SiPM summed output

C6D6/SiPM electronic RF readout design

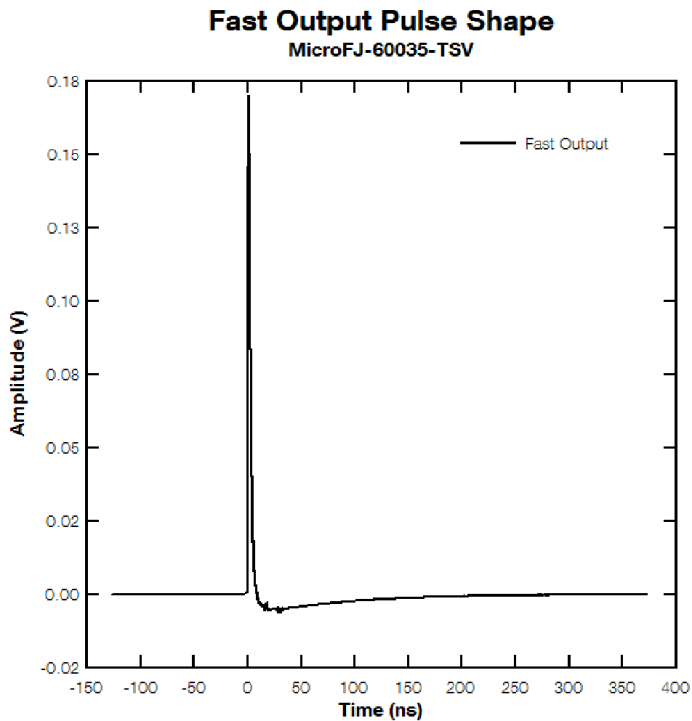
- SiPM output capacitance is of 200 pF/channel (Fast Output) and 4nF/channel (STD Output).
- Direct sum is not reliable as it leads to a very high capacitance in the output and a very time extended output (slows down the output), additionally dark-current from non-firing pixels is added to the final signal, thus worsening the noise a lot.
- Need of a special impedance-matching network to keep initial time response of the fast SiPM output



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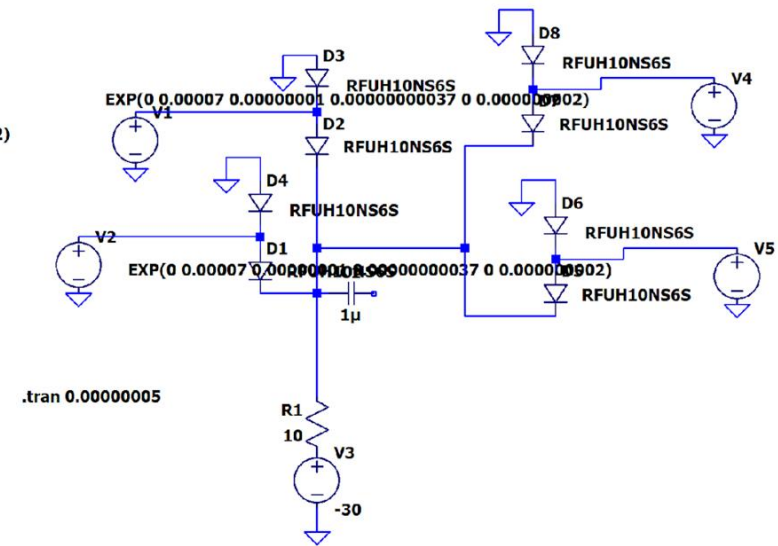


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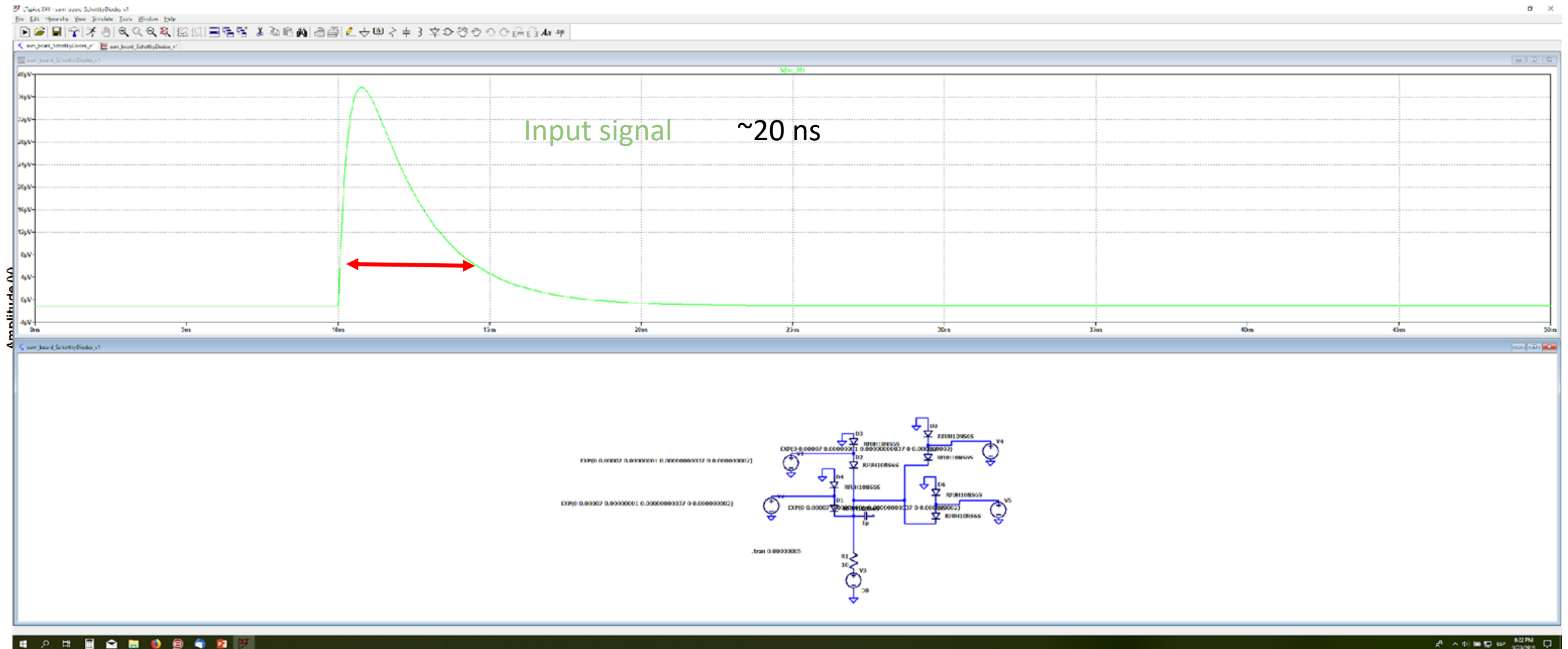
```
EXP(0 0.00007 0.00000001 0.00000000037 0 0.000000002)  
EXP(0 0.00007 0.00000001 0.00000000037 0 0.000000002)
```

SPICE simulation for 4 pixels



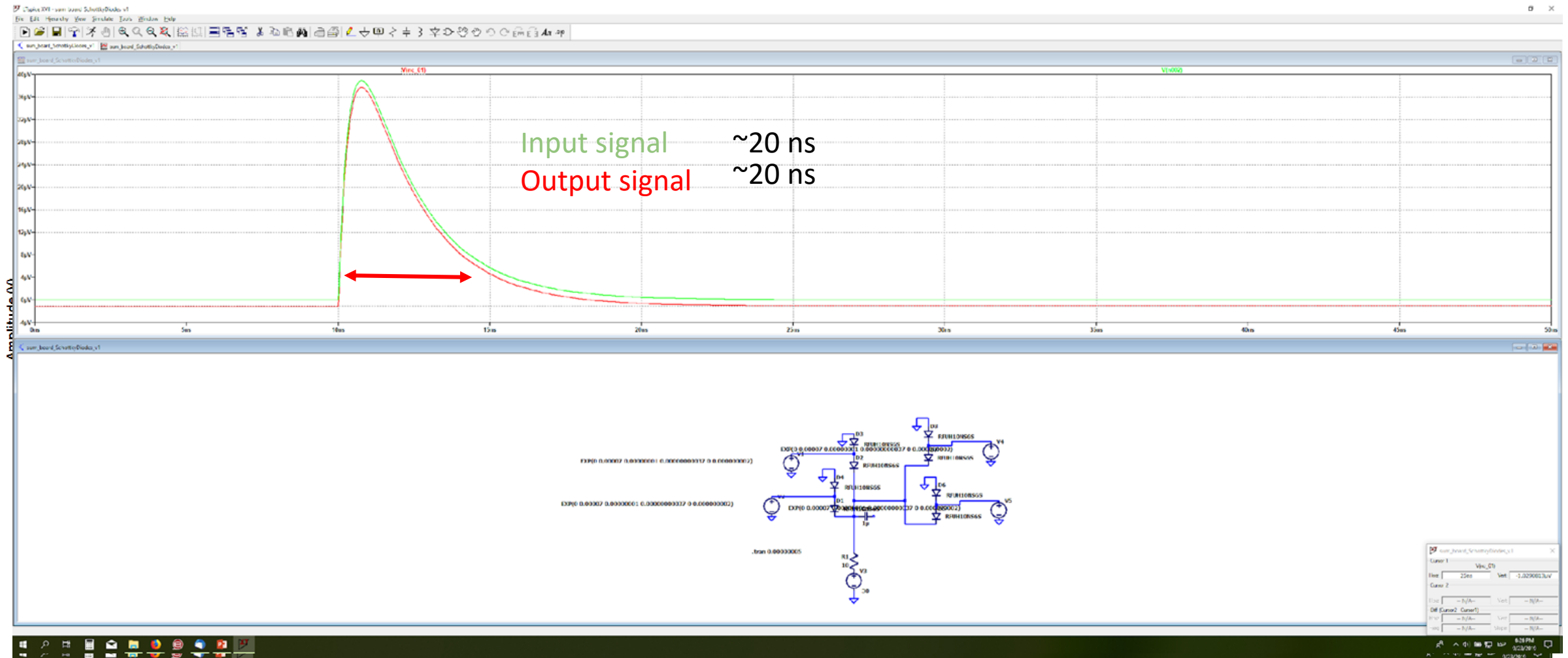
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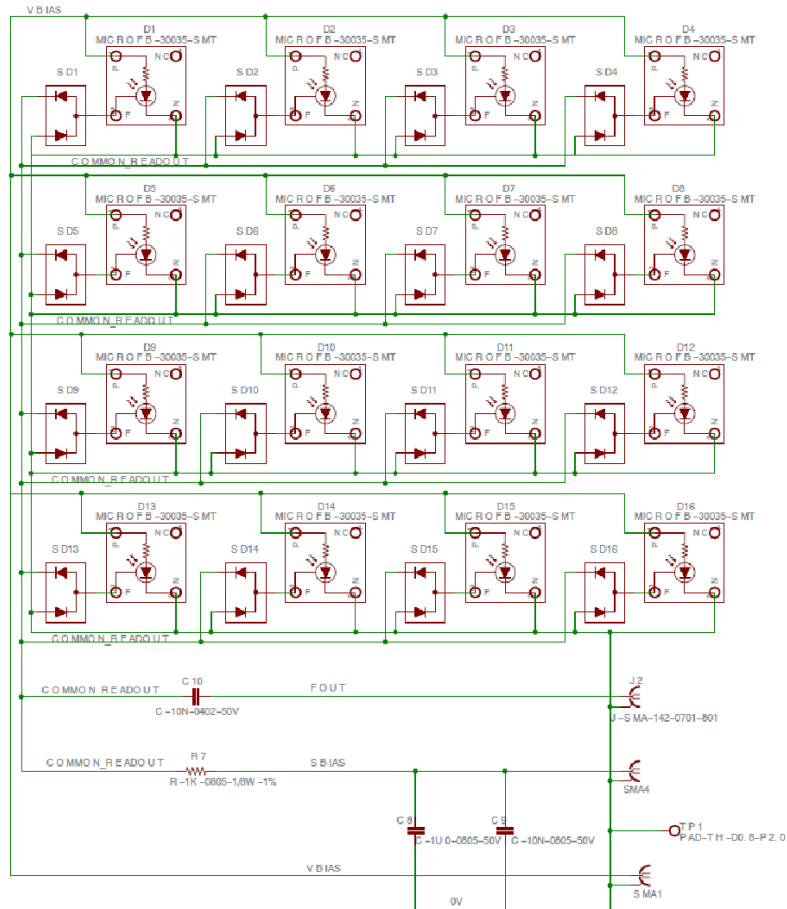
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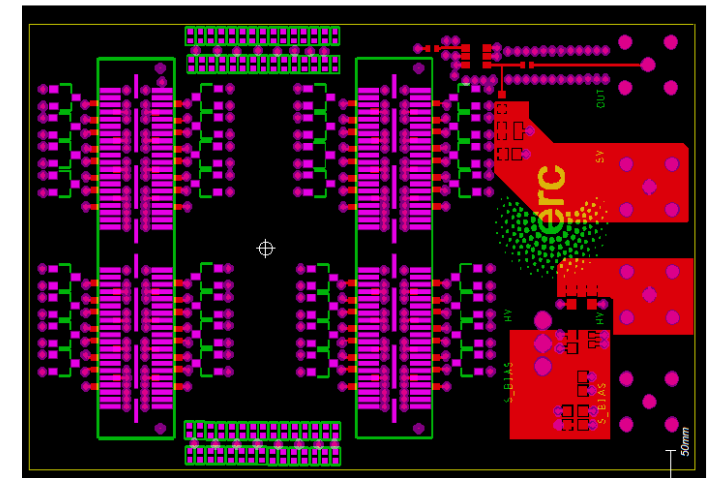
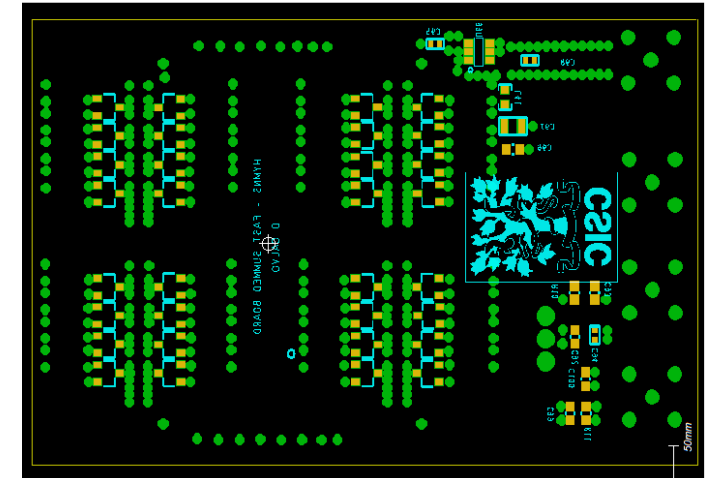
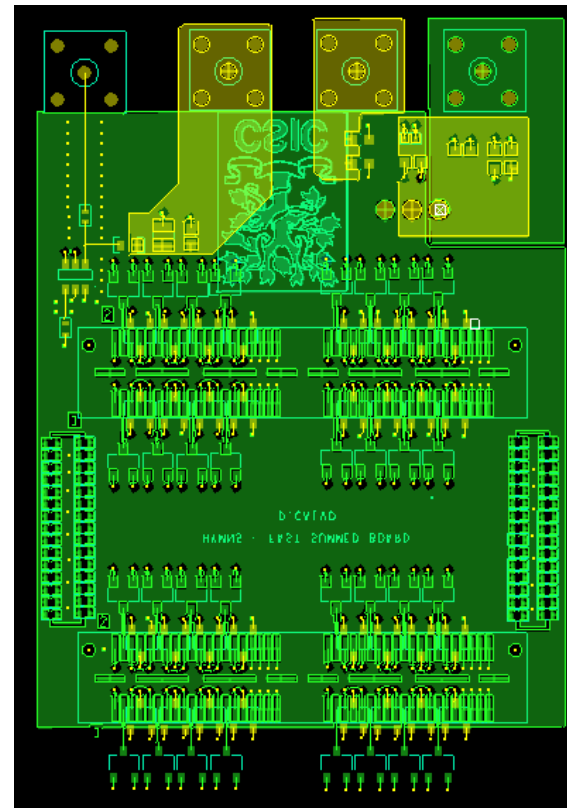


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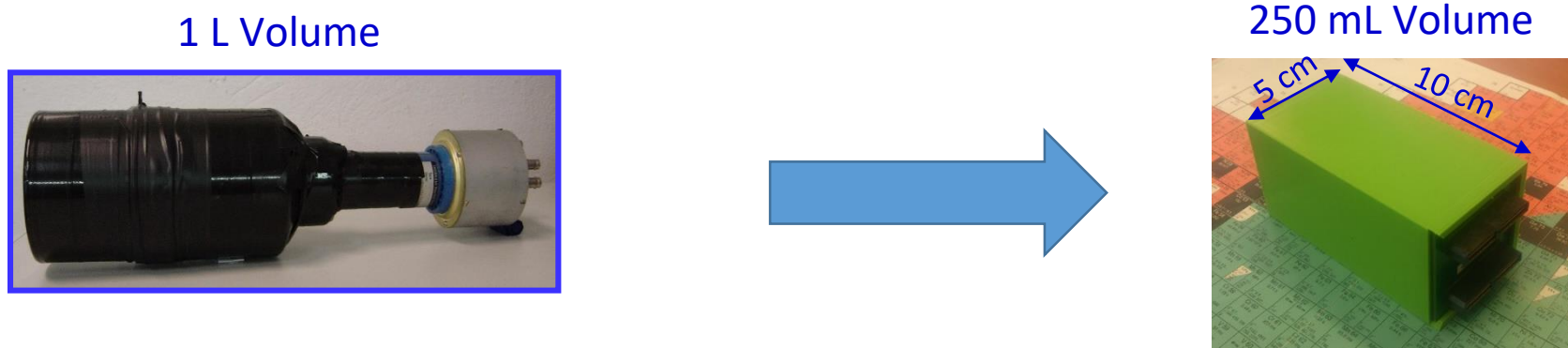
$V_{FastOut}$
 $V_{amp} = +7V$
 $V_{BiasSchottky}$
 $V_{BiasSiPM}$



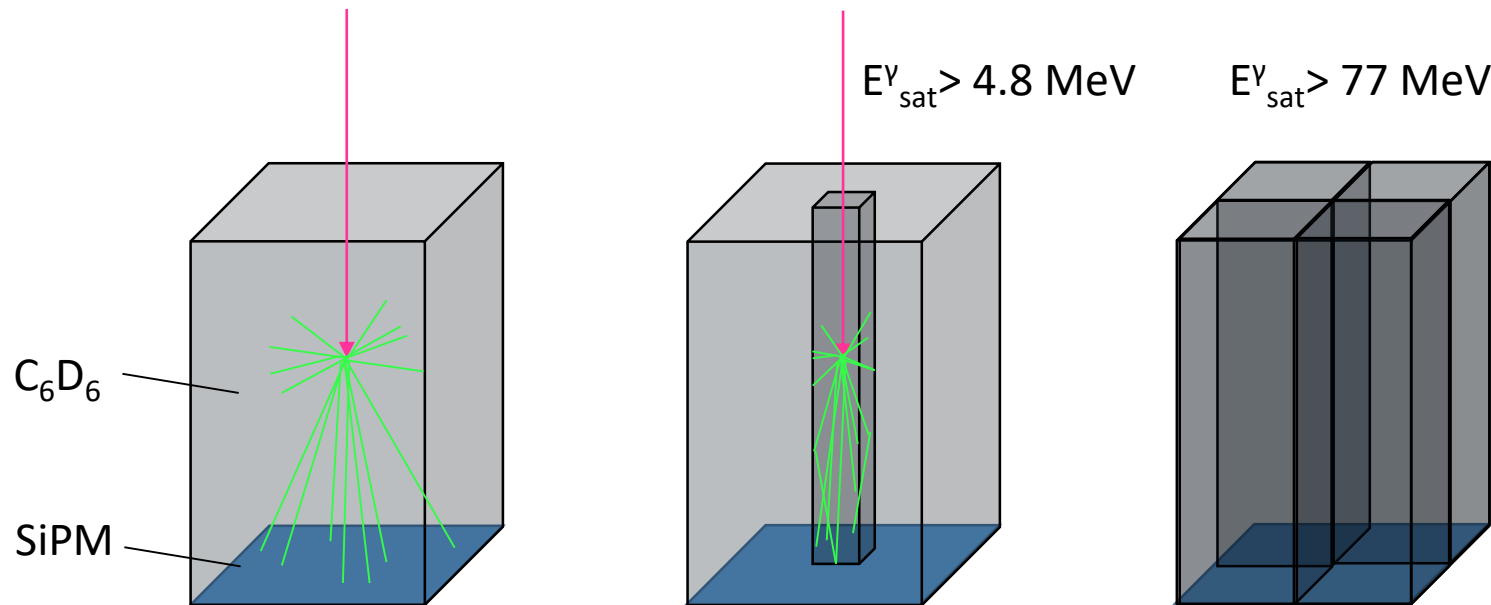
→ Encapsulation optimization for high-count rate capability

C6D6/SiPM encapsulation design and optimization for high count rates

- Reduced size of the sensitive (C6D6) volumen: 250 ml represents 1/4th of C-fiber C6D6+PMT detectors



- Pixelation of the sensitive (C₆D₆) volume, helps? let's test it



C₆D₆ (BC535 equivalent)

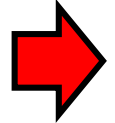
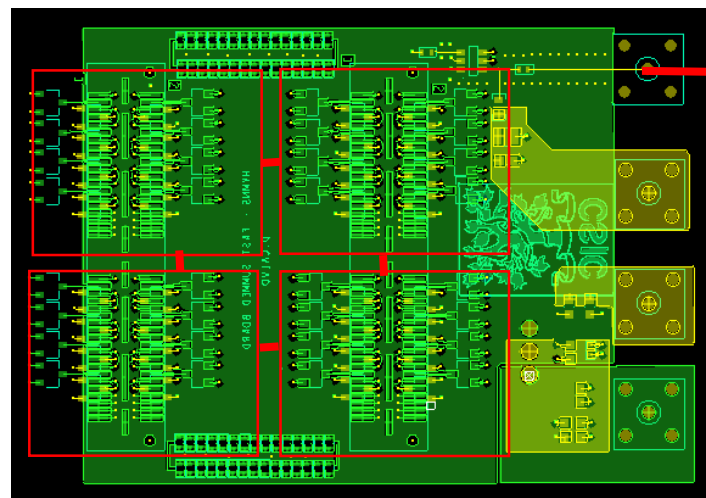
PROPERTIES	□-315
Light Output (% Anthracene)	60
Scintillation Efficiency (photons/1 MeV e ⁻)	9.200
Wave-length of Maximum Emission (nm)	475
Decay Time, Short Component (ns)	3.5
Bulk Light Attenuation Length (m)	>3
Specific Gravity	0.954
Refractive Index	1.498
Flash Point (°C)	-11
Boiling Point (°C at 1 atm)	79

SiPM

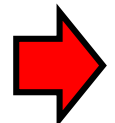
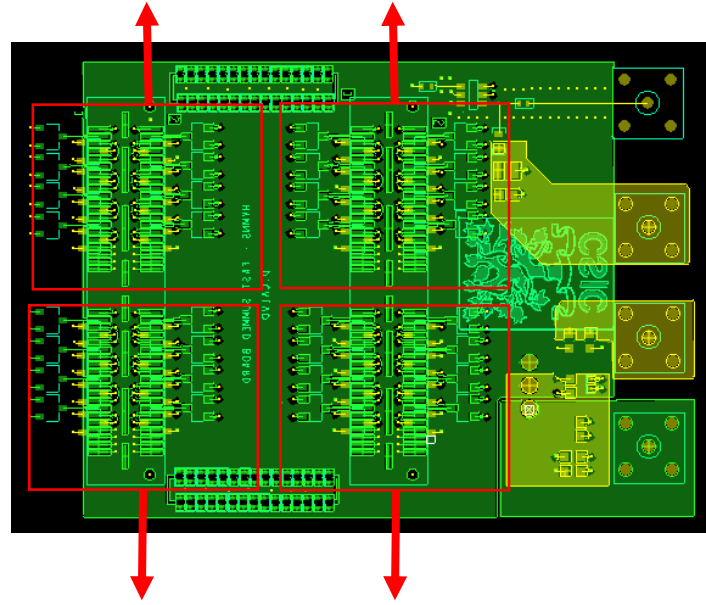
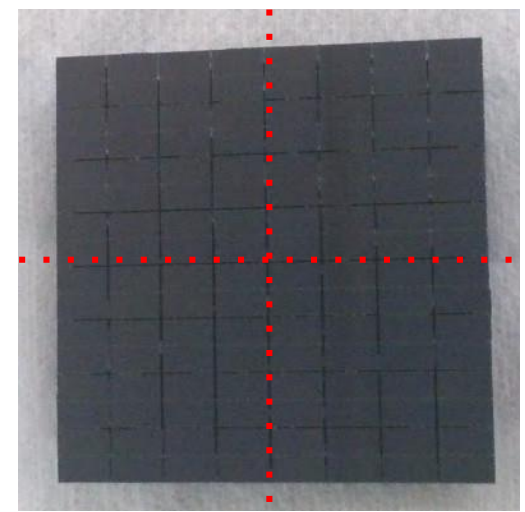


Product Code	Microcell size (Total number per pixel)
6 mm Sensor Arrays	
ArrayJ-60035-4P-BGA	35 um
ArrayJ-60035-64P-PCB	(22,292 microcells)

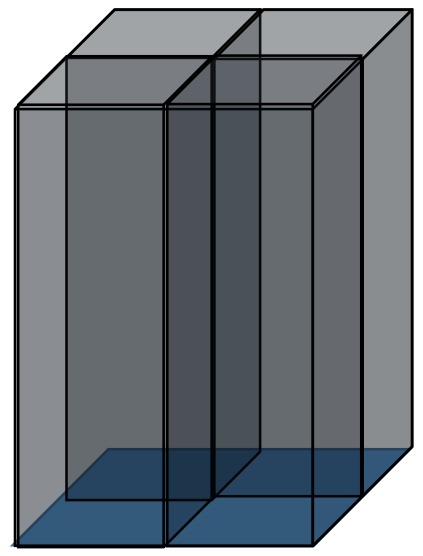
C6D6/SiPM encapsulation design and optimization for high count rates



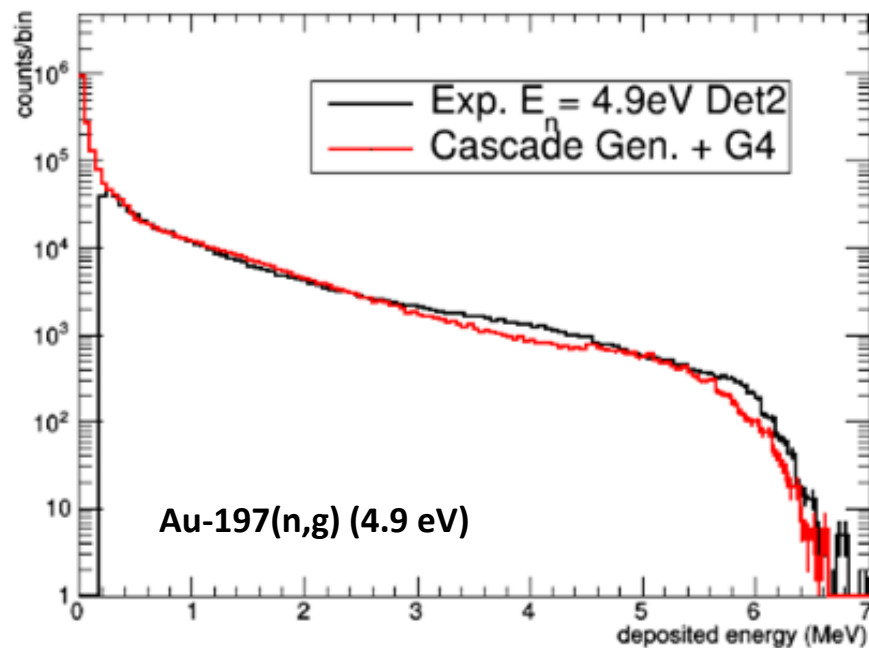
Jumper for summing up reading



4 independent C6D6 detection cells



- Threshold correction depends strongly on the isotope and the detection threshold.
- Example: Pu-242(n,g): After normalization to Au → threshold correction still 4-7% using 150-250 keV threshold



	f_{thr}		
	250 keV	200 keV	150 keV
^{242}Pu	1.150(4)	1.121(4)	1.090(3)
^{197}Au	1.078(3)	1.066(3)	1.052(3)
$^{242}\text{Pu}/^{197}\text{Au}$	1.067(4)	1.052(4)	1.035(4)

$$Y(E_n) = \frac{1}{N_{sample}} \frac{1}{f_{th}} \frac{C(E_n) - B(E_n)}{\varphi(E_n)\varepsilon(E_n)}$$

Large correction in some cases (!)

Proposal:

In parallel to the C6D6+SiPM commissioning.



Measurement of reference capture spectra using LaCl3+SiPM together with the C6D6/SiPM detectors.



Spectroscopic information about the nuclei under study.

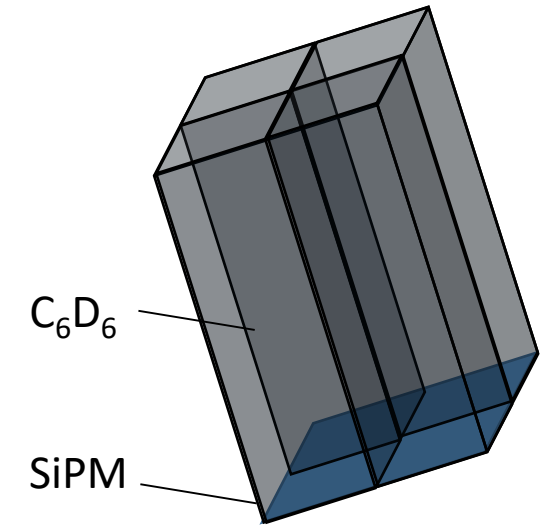
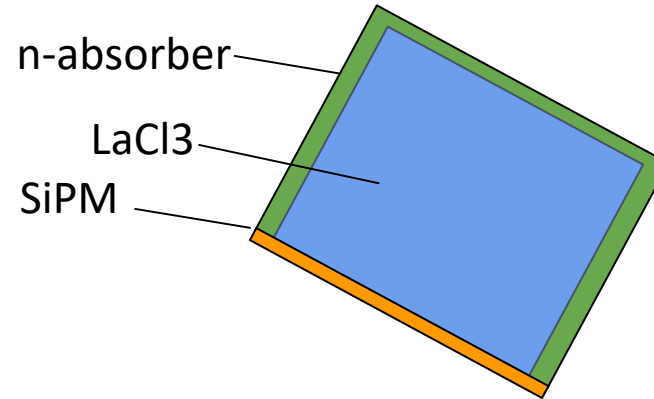


Improve the modeling of neutron capture cascades.



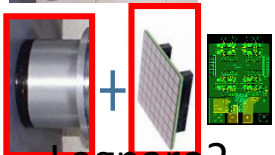
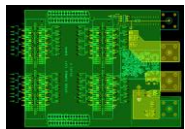
Further Improvement of threshold corrections for TED technique.

Sample under study

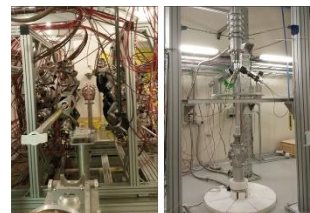


C6D6+SiPM development Workplan

Task	Dates						
PCB Fast Sum	< 15 October IFIC						
PCB Fast Sum test in Lab		15-30 October @ IFIC					
1st test with C6D6 Bicron + SiPM			11-24 November'19@ CERN				
ENCAPSULATION 4 fold C6D6-cell (customized)				Dec.19 – June.20 (?)			
2nd test: C6D6+SiPM & n- sensitivity					July- Dec.'20@ CNA-Seville		
3rd Test: (>LS2, during target #3 commissioning)						Jan- June'21 @ n_TOF	
Nb-94 (n,g) Mo-95-98 (n,g) Proposals							Near future

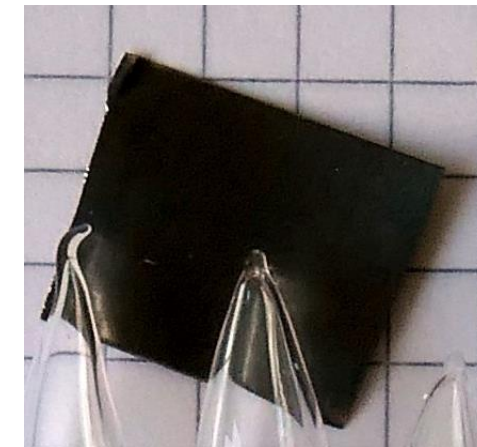


Legnaro?
Bicron?



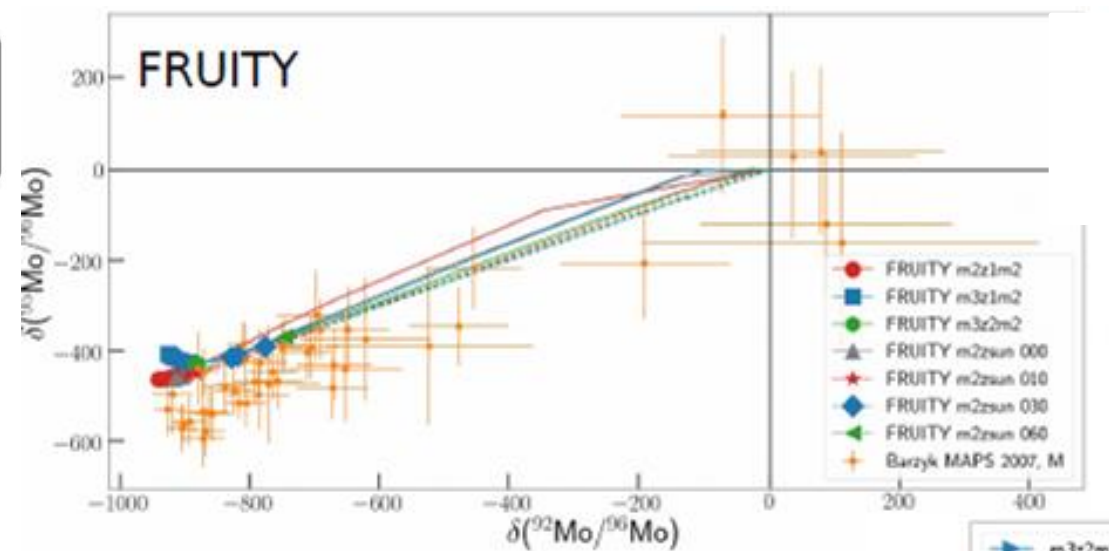
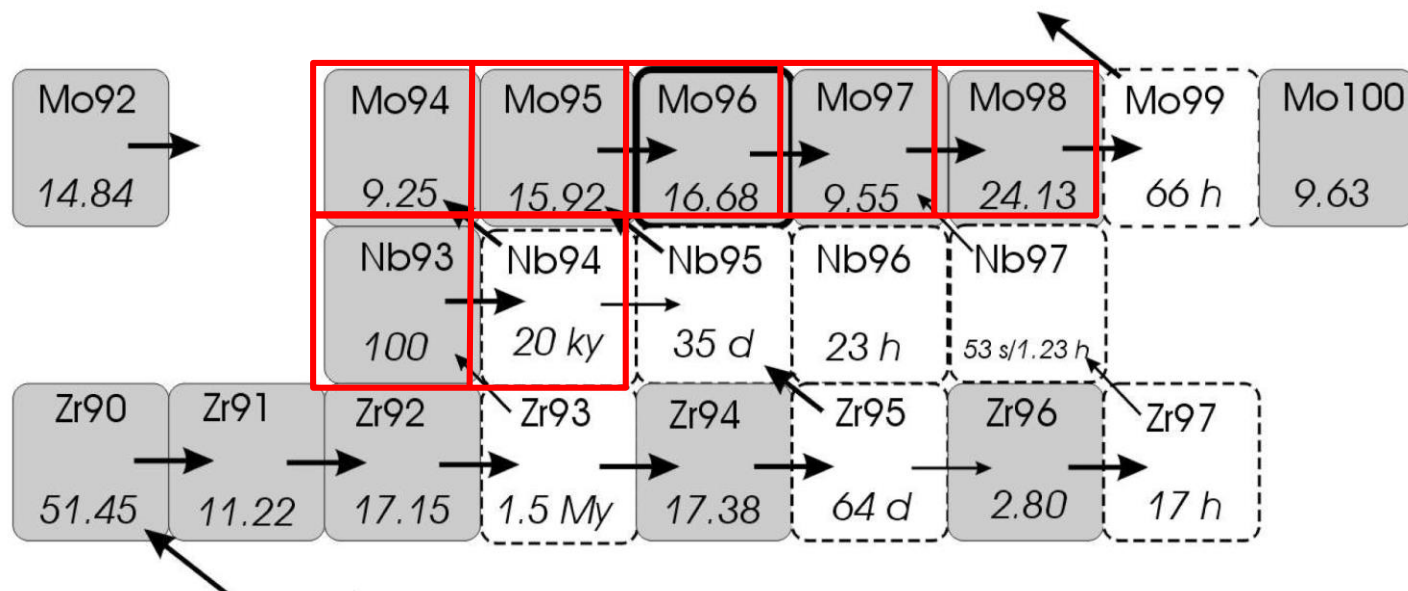
- **Nb-94(n,g):**

- Sample available: Nb-93(n,g)Nb-94 @ ILL
 - 5 ultrahigh purity Nb samples, each 5-10 MBq ⁹⁴Nb, ≈30 MBq ⁹⁵Nb, ≈100 MBq ^{93m}Nb
- Radioactive isotope → **First measurement ever**
- Nugrid calculations on the XS impact to be performed



- **Mo-95-98**

- NPA-IX (A. Tattersall): Mo-96 s-process only (powerful tool)
- Models have problems in reproducing the 95Mo/96Mo ratio from pre-solar grains → Increase of Mo-95(n,g) ~30%
- **Main request from sensitivity study: re-measure Mo-94(n,g), Mo-95(n,g), Mo-96(n,g), Mo-97(n,g), Mo-98(n,g)**



backup stuff

Uncertainties in s-process nucleosynthesis in low-mass stars determined from Monte Carlo variations

G. Cescutti,^{1★†} R. Hirschi,^{2,3†} N. Nishimura,^{4†} J. W. den Hartogh,^{2,5†} T. Rauscher,^{6,7†}
A. St. J. Murphy^{8†} and S. Cristallo^{9,10}

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²Astrophysics group, Lennard-Jones Laboratories, Keele University, ST5 5BG Staffordshire, UK

³Kavli Institute for the Physics and Mathematics of the Universe (WPI), University of Tokyo, 5-1-5 Kashiwanoha, Kashiwa 277-8583, Japan

⁴Yukawa Institute for Theoretical Physics, Kyoto University, Kyoto 606-8502, Japan

⁵Konkoly Observatory, Konkoly Thege Miklós út 15-17, H-1121 Budapest, Hungary

⁶Department of Physics, University of Basel, Klingelbergstr. 82, CH-4056 Basel, Switzerland

⁷Centre for Astrophysics Research, University of Hertfordshire, College Lane, Hatfield AL10 9AB, UK

⁸SUPA, School of Physics and Astronomy, University of Edinburgh, Edinburgh EH9 3FD, UK

⁹INAF, Osservatorio Astronomico d'Abruzzo, I-64100 Teramo, Italy

¹⁰INFN-Sezione di Perugia, I-06123 Perugia, Italy

Table A1. The **key reaction rates for the standard model**. Key rates in levels 1–3 are shown, along with their correlation factors $r_{\text{cor}0}$, $r_{\text{cor}1}$, and $r_{\text{cor}2}$, respectively. Not all s-process nuclides analysed are listed but only those for which key rates were found. Also shown for each rate are the ground state contributions X_0 to the stellar rate of the (n,γ) reaction and uncertainty factors of the β -decay rate at two plasma temperatures, respectively.

Nuclide	$r_{\text{cor},0}$	$r_{\text{cor},1}$	$r_{\text{cor},2}$	Key rate Level 1	Key rate Level 2	Key rate Level 3	X_0 (8, 30 keV)	Weak rate uncertainty factor (8, 30 keV)
⁹⁵ Mo	0.14	0.67		⁹⁵ Mo(n, γ) ⁹⁶ Mo		⁶⁴ Ni(n, γ) ⁶⁵ Ni	1.00, 1.00	
⁹⁶ Mo	−0.85						1.00, 1.00	
⁹⁷ Mo	0.29	0.65		⁹⁶ Mo(n, γ) ⁹⁷ Mo		⁶⁴ Ni(n, γ) ⁶⁵ Ni	1.00, 1.00	
⁹⁸ Mo	−0.94			⁹⁷ Mo(n, γ) ⁹⁸ Mo			1.00, 1.00	
	−0.87			⁹⁸ Mo(n, γ) ⁹⁹ Mo			1.00, 1.00	
	−0.94						1.00, 1.00	

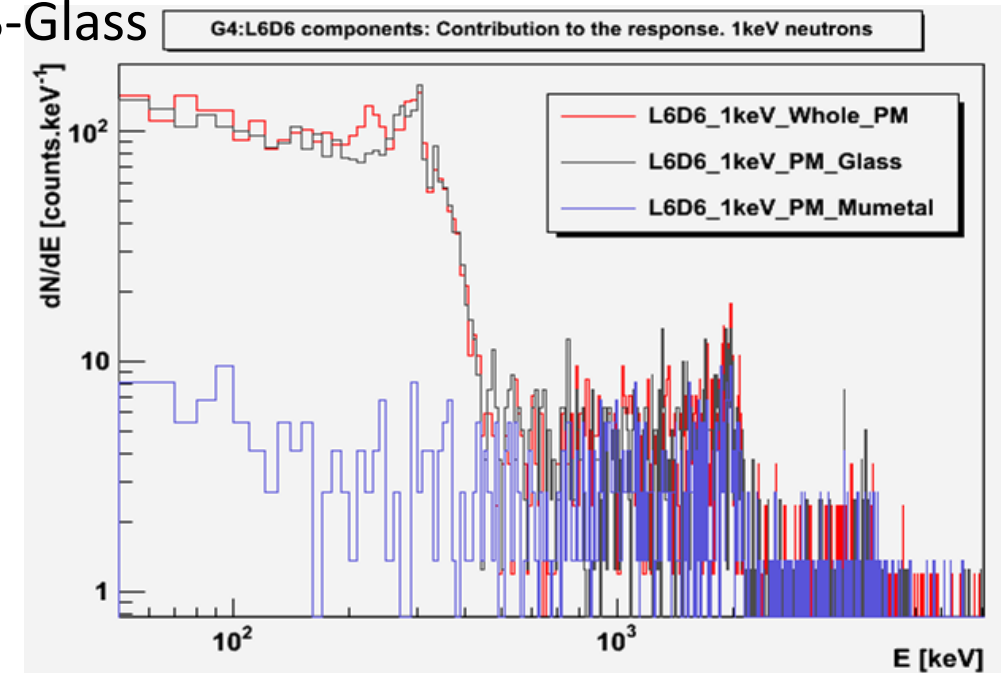
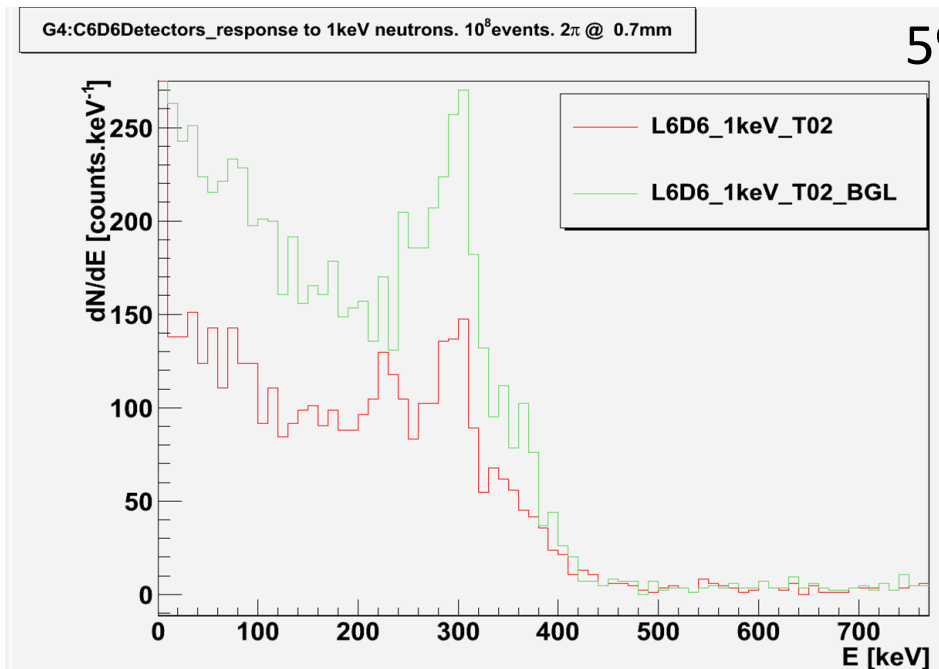
Aspect 1: neutron sensitivity

L6D6 Response to Neutrons (C. Guerrero & J.Lerendegui-Marco, US):

- PMT : empty glass bottle surrounded by a thin Mumetal layer

Impact of Boron

5%(BGL) vs 2% B-Glass

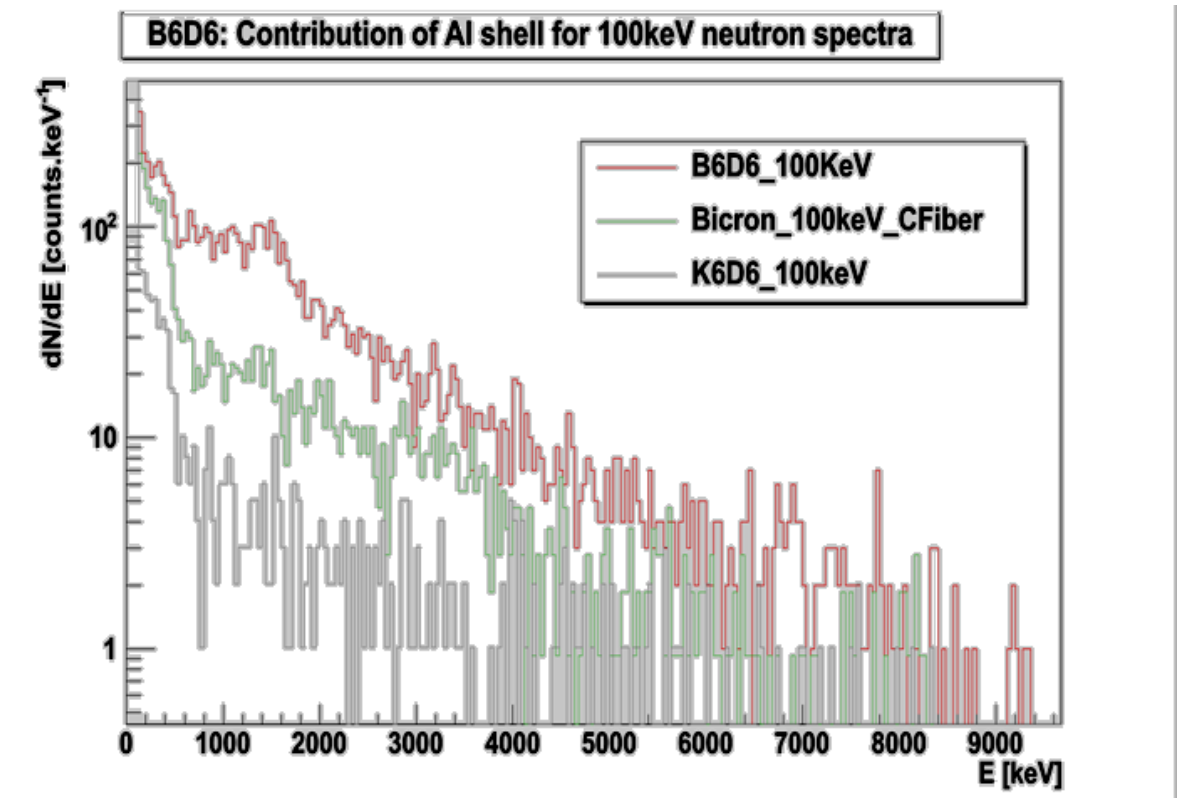
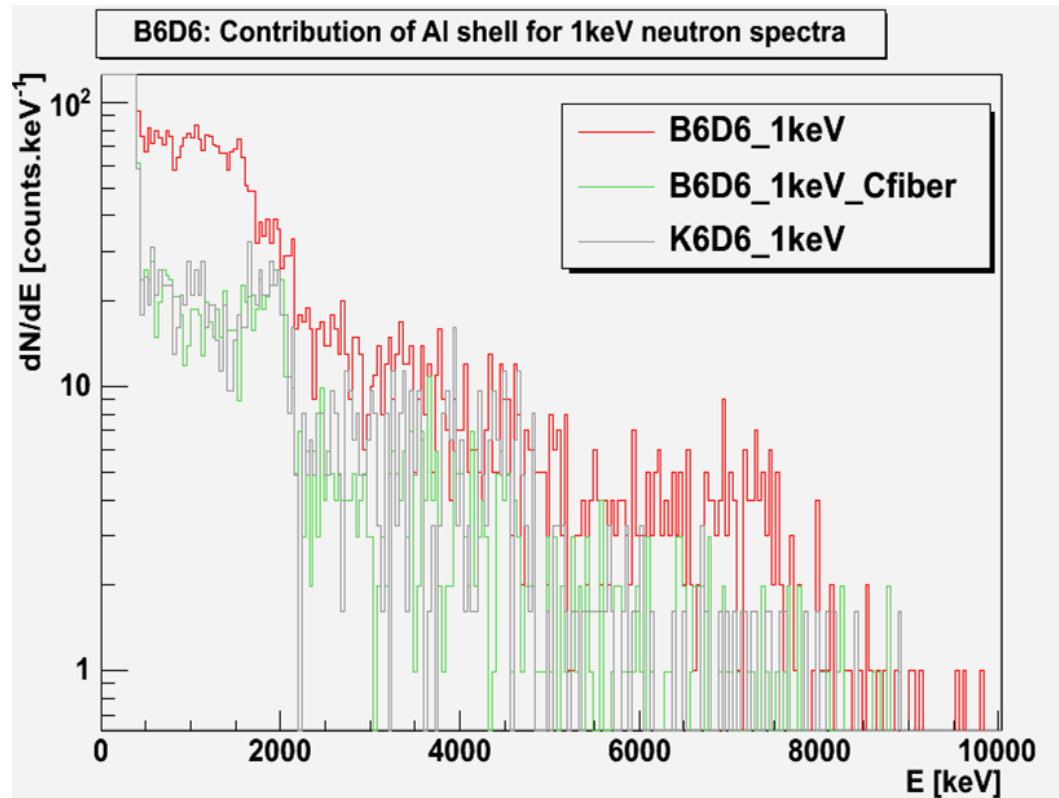


Thus, avoiding PMT (thereby reducing also total amount of CF) should help to reduce NS further down(!)

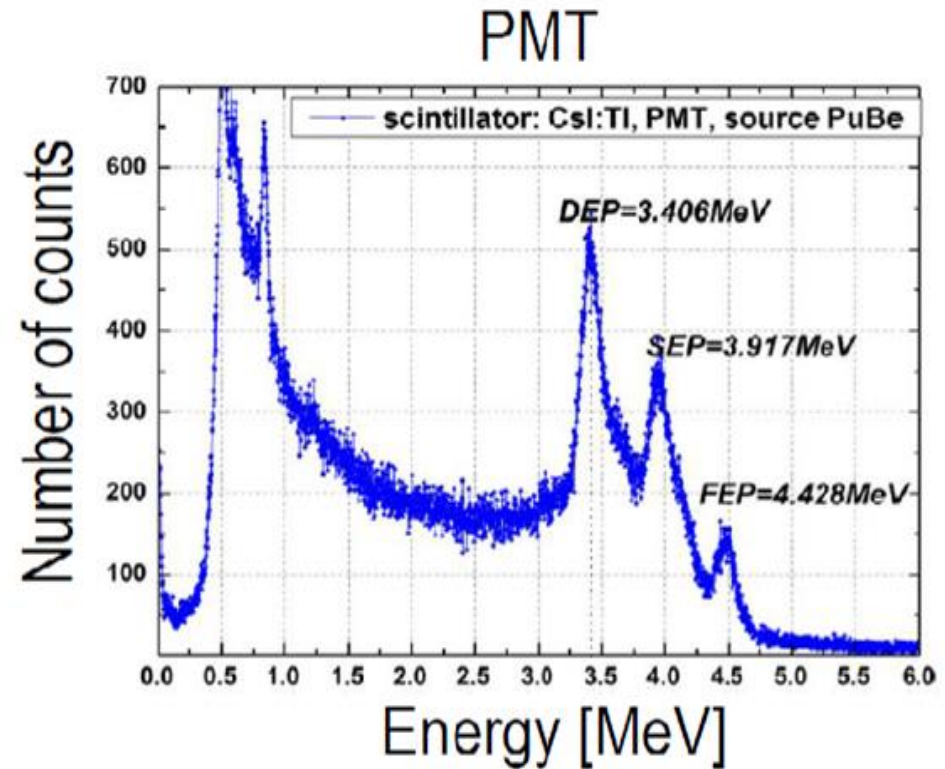
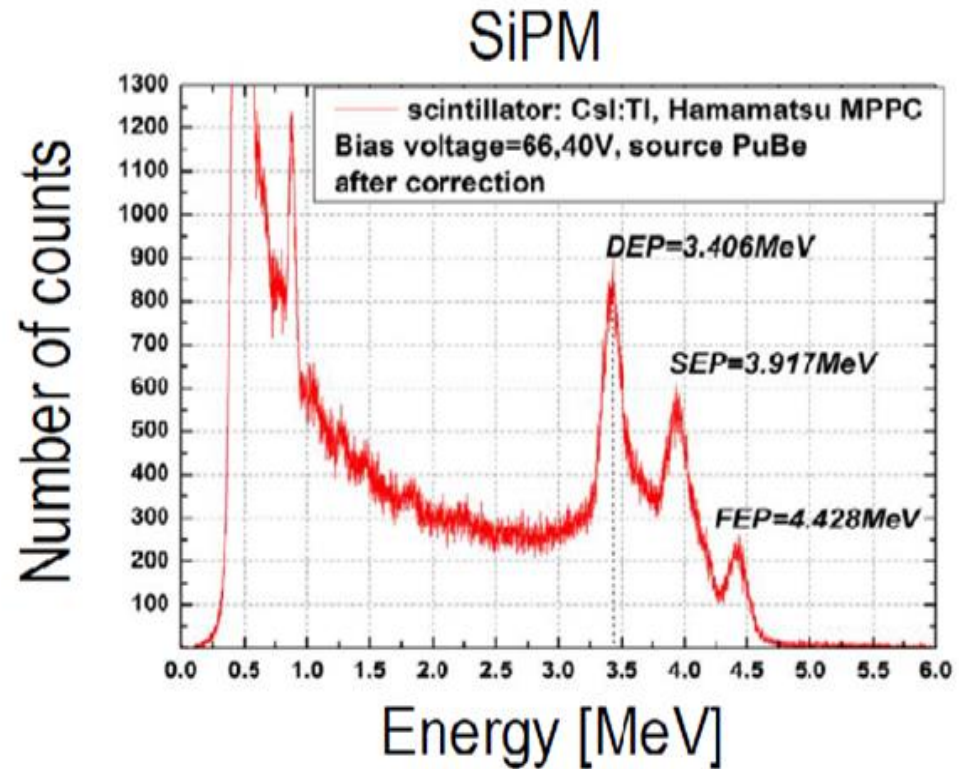
Aspect 1: neutron sensitivity

L6D6 Response to Neutrons (C. Guerrero & J.Lerendegui-Marco, US):

Influence of Al/Carbon Fiber



SiPM vs. PMT in γ -ray detection



Example of energy spectra from Grodzicka et al. 2017 [Nuclear Inst. and Methods in

Physics Research, A 874 (2017) 137–148]

Sensor Size	Microcell Size	Parameter	Overtoltage	Min.	Typical	Max.	Units	
3mm	20µm	Gain (anode-cathode)	Vbr + 2.5V	9.1x10 ⁶				
	35µm			2.8x10 ⁶				
	20µm		Vbr + 5.0V	1.7x10 ⁶				
	35µm			5.3x10 ⁶				
6mm	35µm		Vbr + 2.5V	2.8x10 ⁶				
			Vbr + 5.0V	5.3x10 ⁶				
3mm	20µm		Dark Current	Vbr + 2.5V	0.2	0.3		µA
	35µm							
	20µm	Vbr + 5.0V		1.1	1.8		µA	
	35µm							
6mm	35µm	Vbr + 2.5V		0.9	1.3		µA	
		Vbr + 5.0V		4.1	5.8		µA	
3mm	20µm, 35µm	Rise time ¹ - anode-cathode output			100			ps
6mm	35µm				300			ps
3mm	20µm	Microcell recharge time constant ²		12			ns	
	35µm			37			ns	
6mm	35µm			48			ns	
3mm	20µm	Capacitance ³ (anode output)	Vbr + 2.5V	TBD			µF	
	35µm			1000			µF	
6mm	35µm			4000			µF	
3mm	20µm	Capacitance ³ (fast terminal)	Vbr + 2.5V	TBD			µF	
	35µm			50			µF	
6mm	35µm			200			µF	
3mm	20µm	Fast output pulse width (FWHM)		1.4			ns	
	35µm			1.4			ns	
6mm	35µm			3.0			ns	
3mm	20µm	Crosstalk	Vbr + 2.5V	5			%	
	35µm			7			%	
	20µm		Vbr + 5.0V	10			%	
	35µm			22			%	
6mm	35µm		Vbr + 2.5V	7			%	
			Vbr + 5.0V	22			%	
3mm	20µm, 35µm		Afterpulsing	Vbr + 2.5V	0.1			%
	20µm, 35µm				1.0			%
6mm	35µm	Vbr + 2.5V		0.1			%	
		Vbr + 5.0V		1.0			%	
3mm	20µm, 35µm	Temperature dependence of Vbr ⁴		-21.5			mV/C	
6mm	35µm							

